Module description

Module title				Abbreviation
Physics of Semiconductor Devices				11-SPD-152-m01
Module coordinator			Module offered by	
Managing Director of the Institute of Ap		plied Physics Faculty of Physics and Astronomy		
ECTS Method of grading Or		Only after succ. compl. of module(s)		
6 numerical grade				
Duration Module level		Other prerequisites		
1 semester undergraduate				
Contents				
amples. The basic part introduces the crystal structures and band and phonon dispersions of technologically re- levant semiconductors. The following part discusses the principles of charge transport involving non-equilibrium effects based on the charge carrier density of the thermal equilibrium. The part on technology gives an insight into the methods of production of semiconductor materials and presents the most important methods of planar technology. It discusses the way of functioning of the following components, sorted according to volume com- ponents, interface components and application fields: Rectifier diodes, Zener diodes, varistor, varactor, tunnel diodes, IMPATT, Baritt- and Gunn diodes, photodiode, solar cell, LED, semiconductor injection laser, transistor, JFET, Thyristor, Diac, Triac, Schottky diode, MOSFET, MESFET, HFET. It highlights the importance of low-dimensio- nal charge carrier systems for technology and basic research and shows recent developments in the components sector				
Intended learning outcomes				
The students know the characteristics of semiconductors, they have gained an overview of the electronic and phonon band structures of important semiconductors and the resulting electronic, optical and thermal properties. They know the principles of charge transport as well as the Poisson, Boltzmann and continuity equation for the solution of questions. They have gained insights into the methods of semiconductor production and are familiar with the theories of planar technology and recent developments in this field, they have a basic understanding of component production. They understand the structure and way of functioning of the main components of electronics (diode, transistor, field-effect transistor, thyristor, diac, triac), of microwave applications (tunnel, Impatt, Baritt or Gunn diode) and of optoelectronics (photo diode, solar cell, light-emitting diode, semiconductor injection laser), they know the realisation possibilities of low-dimensional charge carrier systems on the basis of semiconductors and their technological relevance, they are familiar with current developments in the field of components.				
Courses (type, number of weekly contact hours, language — if other than German)				
V (3) + R (1) Module taught in: German or English				
Method of assessment (type, scope, language — if other than German, examination offered — if not every semester, information on whether module is creditable for bonus)				
written examination (approx. 90 to 120 minutes) or oral examination of one candidate each (approx. 30 minutes) or oral examination in groups (groups of 2, approx. 30 minutes per candidate) or project report (approx. 8 to 10 pages) or presentation/talk (approx. 30 minutes). If a written examination was chosen as method of assessment, this may be changed and assessment may instead take the form of an oral examination of one candidate each or an oral examination in groups. If the method of assessment is changed, the lecturer must inform students about this by four weeks prior to the original examination date at the latest. Assessment offered: Once a year, summer semester Language of assessment: German and/or English				

Additional information

Referred to in LPO I (examination regulations for teaching-degree programmes)

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Module appears in

Bachelor' degree (1 major) Physics (2015)

Bachelor' degree (1 major) Nanostructure Technology (2015) Master's degree (1 major) Functional Materials (2016)

Bachelor' degree (1 major) Physics (2020)

Bachelor' degree (1 major) Nanostructure Technology (2020)

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